CGHV27100

100 W, 2500-2700 MHz, 50 V, GaN HEMT for LTE

Cree's CGHV27100 is a gallium nitride (GaN) high electron mobility transistor (HEMT) is designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGHV27100 ideal for 2.5 - 2.7 GHz LTE, 4G Telecom and BWA amplifier applications. The transistor is input matched and supplied in a ceramic/ metal pill and flange packages.

Package Type: 440162 and 440161
PN: CGHV27100F and CGHV27100P

Typical Performance Over 2.5 - 2.7 GHz (T_C = 25°C) of Demonstration Amplifier

Parameter	2.5 GHz	2.6 GHz	2.7 GHz	Units
Gain @ 44 dBm	18.1	18.0	17.9	dB
ACLR @ 44 dBm	-37.0	-37.0	-37.0	dBc
Drain Efficiency @ 44 dBm	34.0	33.5	32.0	%

Note:
Measured in the CGHV27100-AMP amplifier circuit, under WCDMA 3GPP test model 1, 64 DPCH, 45% clipping, PAR = 7.5 dB @ 0.01% Probability on CCDF, V_{DD} = 50 V, I_{DS} = 500 mA.

Features

RoHS COMPLIANT

- 2.5 - 2.7 GHz Operation
- 18.0 dB Gain
- -37 dBc ACLR at 25 W P_{AVE}
- 33 % Efficiency at 25 W P_{AVE}
- High Degree of DPD Correction Can be Applied

Large Signal Models Available for ADS and MWO

Absolute Maximum Ratings (not simultaneous) at 25˚C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	125	Volts	25˚C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25˚C
Storage Temperature	T_{STG}	-65, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_{GMAX}	16	mA	25˚C
Maximum Drain Current[1]	I_{DMAX}	6	A	25˚C
Soldering Temperature[2]	T_S	245	˚C	
Screw Torque	τ	80	in-oz	
Thermal Resistance, Junction to Case[3]	$R_{\theta JC}$	2.34	˚C/W	85˚C, P_{DISS} = 48 W
Thermal Resistance, Junction to Case[4]	$R_{\theta JC}$	2.95	˚C/W	85˚C, P_{DISS} = 48 W
Case Operating Temperature[5]	T_C	-40, +150	˚C	

Note:
[1] Current limit for long term, reliable operation.
[2] Refer to the Application Note on soldering at http://www.cree.com/rf/document-library
[3] Measured for the CGHV27100P
[4] Measured for the CGHV27100F
[5] See also, the Power Dissipation De-rating Curve on Page 5.

Electrical Characteristics (T_C = 25˚C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1]						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 16 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–	V_{DC}	V_{DS} = 50 V, I_D = 500 mA
Saturated Drain Current[2]	I_{DS}	12	14.4	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BR}	150	–	–	V_{DC}	V_{GS} = -8 V, I_D = 16 mA
RF Characteristics[5] (T_C = 25˚C, F_0 = 2.7 GHz unless otherwise noted)						
Saturated Output Power[3,4]	P_{SAT}	–	135	–	W	V_{DD} = 50 V, I_{DQ} = 500 mA
Pulsed Drain Efficiency[3,4]	η	–	68	–	%	V_{DD} = 50 V, I_{DQ} = 500 mA, P_{OUT} = P_{SAT}
Gain[6]	G	–	18	–	dB	V_{DD} = 50 V, I_{DQ} = 500 mA, P_{OUT} = 44 dBm
WCDMA Linearity[6]	ACLR	–	-37	–	dBc	V_{DD} = 50 V, I_{DQ} = 500 mA, P_{OUT} = 44 dBm
Drain Efficiency[6]	η	–	33	–	%	V_{DD} = 50 V, I_{DQ} = 500 mA, P_{OUT} = 44 dBm
Output Mismatch Stress[3]	VSWR	–	–	10 : 1	Ψ	No damage at all phase angles, V_{DD} = 50 V, I_{DQ} = 500 mA, P_{OUT} = 100 W Pulsed
Dynamic Characteristics						
Input Capacitance[7]	C_{GS}	–	66	–	pF	V_{DS} = 50 V, V_{gs} = -8 V, f = 1 MHz
Output Capacitance[7]	C_{DS}	–	8.7	–	pF	V_{DS} = 50 V, V_{gs} = -8 V, f = 1 MHz
Feedback Capacitance	C_{GD}	–	0.47	–	pF	V_{DS} = 50 V, V_{gs} = -8 V, f = 1 MHz

Notes:
[1] Measured on wafer prior to packaging.
[2] Scaled from PCM data.
[3] Pulse Width = 100 µs, Duty Cycle = 10%
[4] P_{SAT} is defined as I_{GS} = 1.6 mA peak
[5] Measured in CGHV27100-AMP
[6] Single Carrier WCDMA, 3GPP Test Model 1, 64 DPCH, 45% Clipping, PAR = 7.5 dB @ 0.01% Probability on CCDF, V_{DD} = 50 V.
[7] Includes package and internal matching components.

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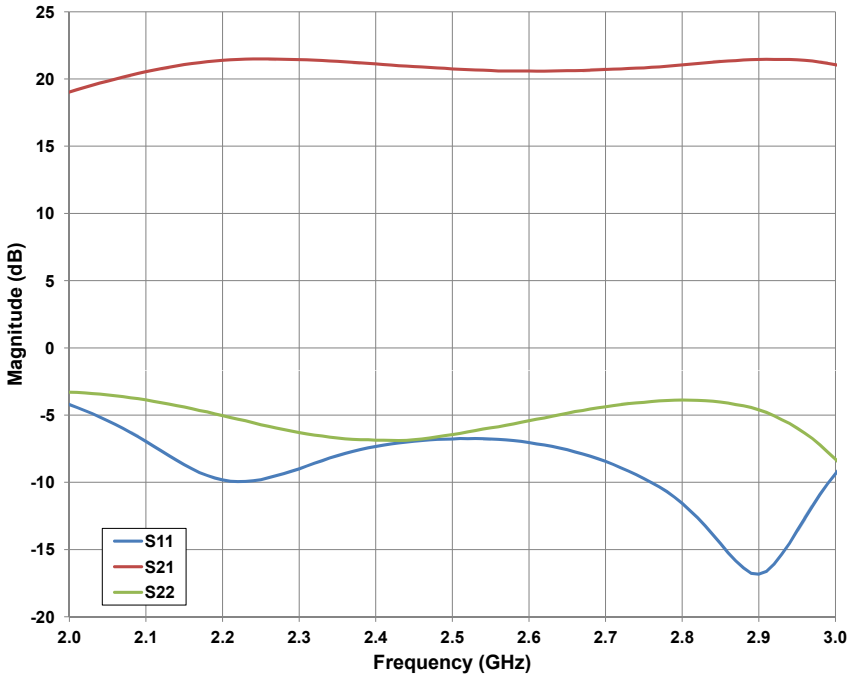
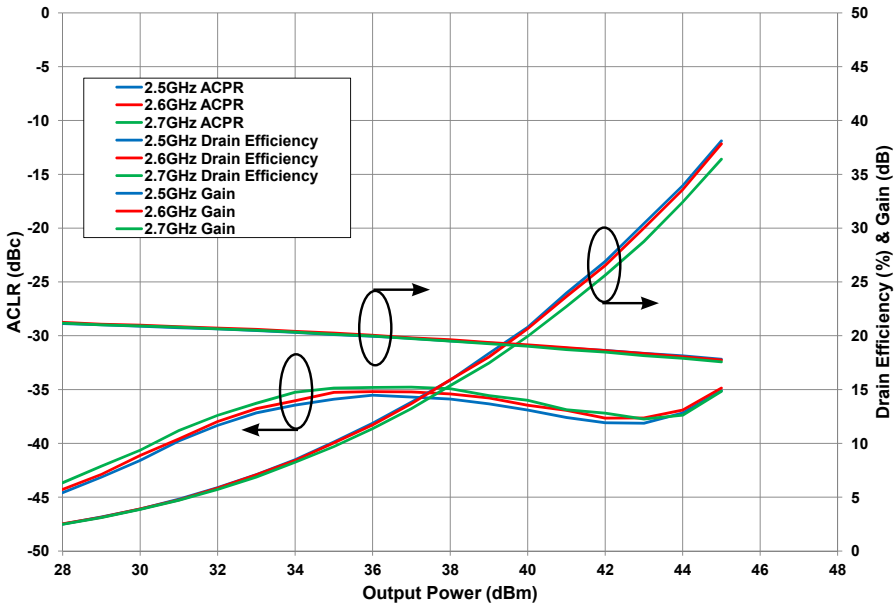
Typical Performance

Figure 1. - Small Signal Gain and Return Losses vs Frequency for the CGHV27100 measured in CGHV27100-AMP Amplifier Circuit
V_{DD} = 50 V, I_{DQ} = 0.5 A



Typical Linear Performance

Figure 2. - Typical Gain, Drain Efficiency and ACLR vs Output Power of the CGHV27100 measured in CGHV27100-AMP Amplifier Circuit
V_{DS} = 50 V, I_{DS} = 0.5 A, 1c WCDMA, PAR = 7.5 dB



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Typical Performance

Figure 3. - Typical Gain, Drain Efficiency and ACLR vs Frequency of the CGHV27100 measured in CGHV27100-AMP Amplifier Circuit. V_{DS} = 50 V, I_{DS} = 0.5 A, P_{AVE} = 25 W, 1c WCDMA, PAR = 7.5 dB

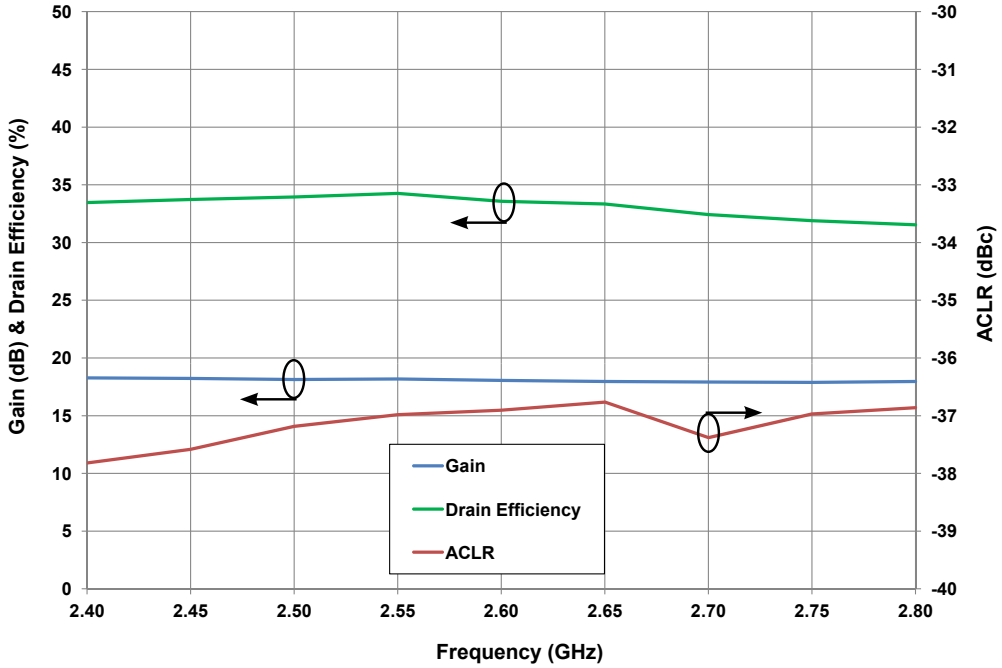
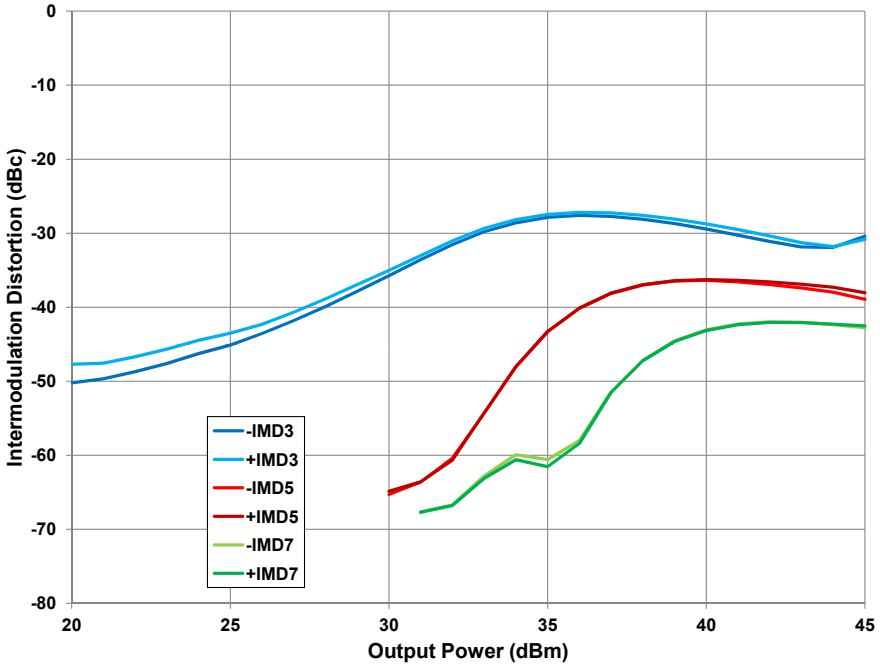


Figure 4. - Typical Two Tone Linearity vs Output Power of the CGHV27100 measured in CGHV27100-AMP1 Amplifier Circuit. V_{DS} = 50 V, I_{DS} = 0.5 A



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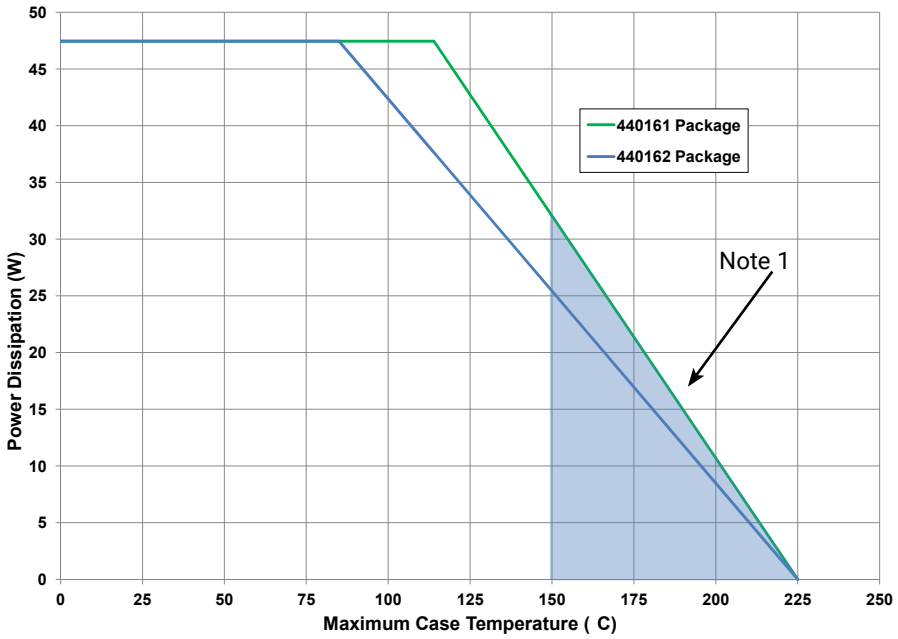
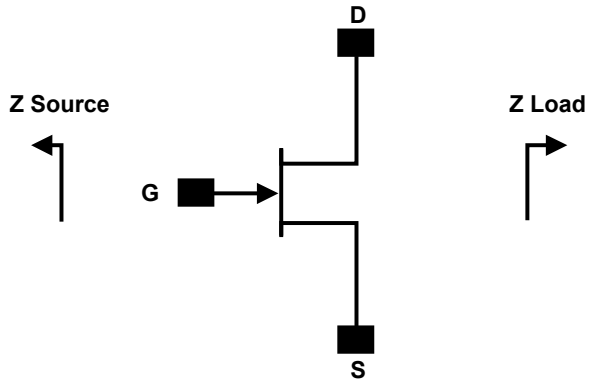
Typical Performance

Figure 5. - Power Dissipation Derating Curve



Note 1. Area exceeds Maximum Case Operating Temperature (See Page 2).

Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
2500	4.01 - j3.88	10.69 - j2.86
2600	3.99 - j3.29	11.16 - j3.17
2700	4.01 - j2.72	11.67 - j3.94

Note[1]: V_{DD} = 50 V, I_{DQ} = 500 mA. In the 440162 package.
Note[2]: Impedances are extracted from CGHV27100-AMP demonstration circuit and are not source and load pull data derived from transistor.

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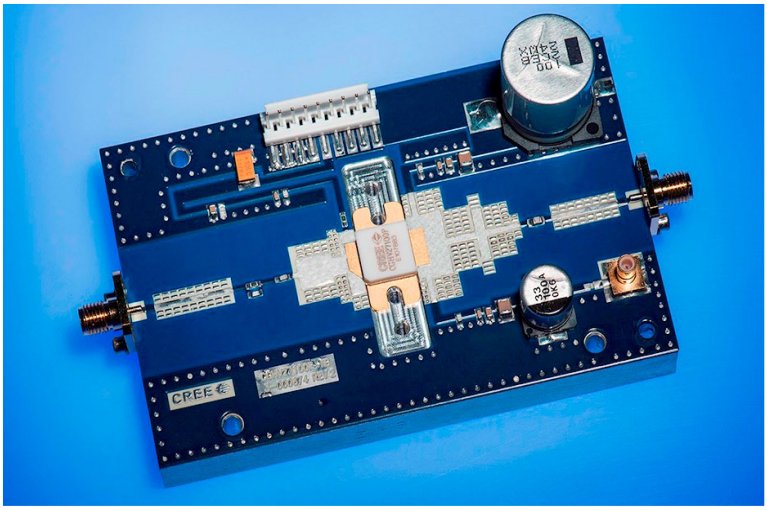
CGHV27100-AMP Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
R1, R2	RES, 10 OHM, +/- 1%, 1/16 W, 0603	2
C1	CAP, 5.6 pF, +/- 0.25 pF, 0603, ATC	1
C2	CAP, 27 pF, +/-5%, 0603, ATC	1
C3	CAP, 10.0 pF, +/-5%, 0603, ATC	1
C8, C13	CAP, 8.2 pF, +/-0.25 pF, 0603, ATC	2
C4, C9, C14	CAP, 470 pF, 5%, 100 V, 0603, X	3
C5, C10, C15	CAP, 33000 pF, 0805, 100 V, X7R	3
C6	CAP, 10 UF, 16 V, TANTALUM	1
C7	CAP, 27 pF, +/-5%, 250 V, 0805, ATC 600 F	1
C11, C16	CAP, 1.0 UF, 100 V, 10%, X7R, 1210	2
C12	CAP, 100 UF, +/-20%, 160 V, ELECTROLYTIC	1
C17	CAP, 33 UF, 20%, ELECTROLYTIC	1
J1, J2	CONN, SMA	2
J3	HEADER RT>PLZ.1CEN LK 9POS	1
	PCB, RO4350, 0.020" THK, CGHV27100F	1
	2-56 SOC HD SCREW 1/4 SS	4
	#2 SPLIT LOCKWASHER SS	4
	CGHV27100F	1

CGHV27100-AMP Demonstration Amplifier Circuit



Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A > 250 V	JEDEC JESD22 A114-D
Charge Device Model	CDM	1 < 200 V	JEDEC JESD22 C101-C

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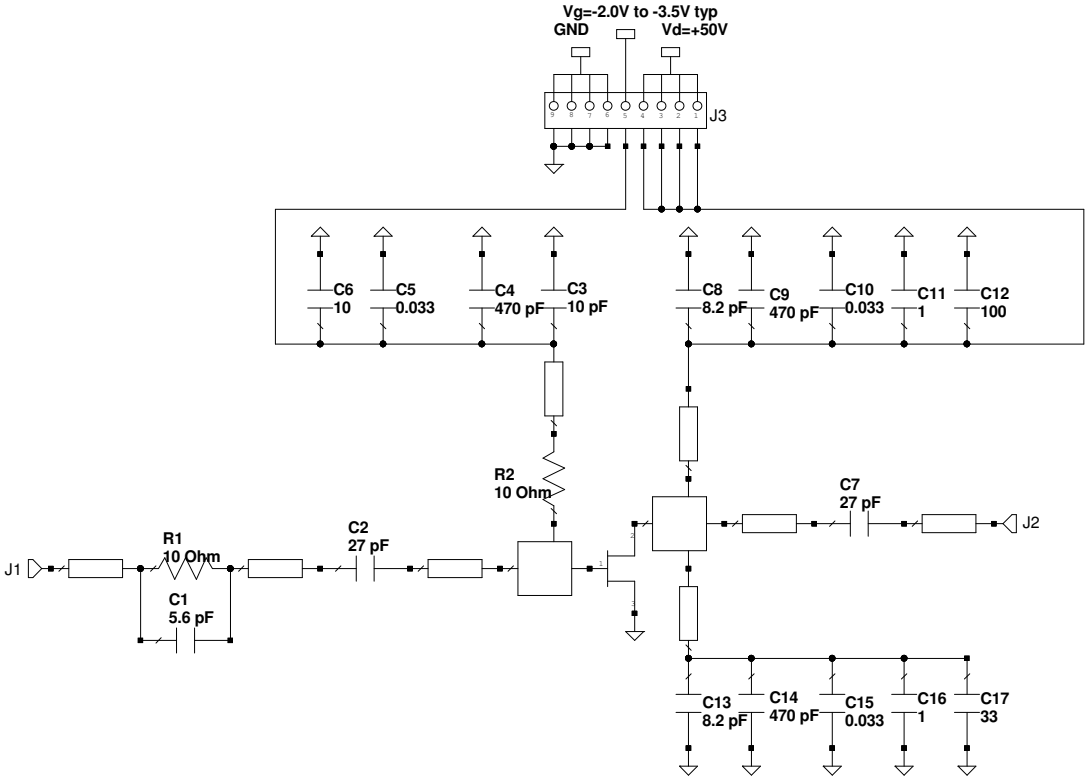
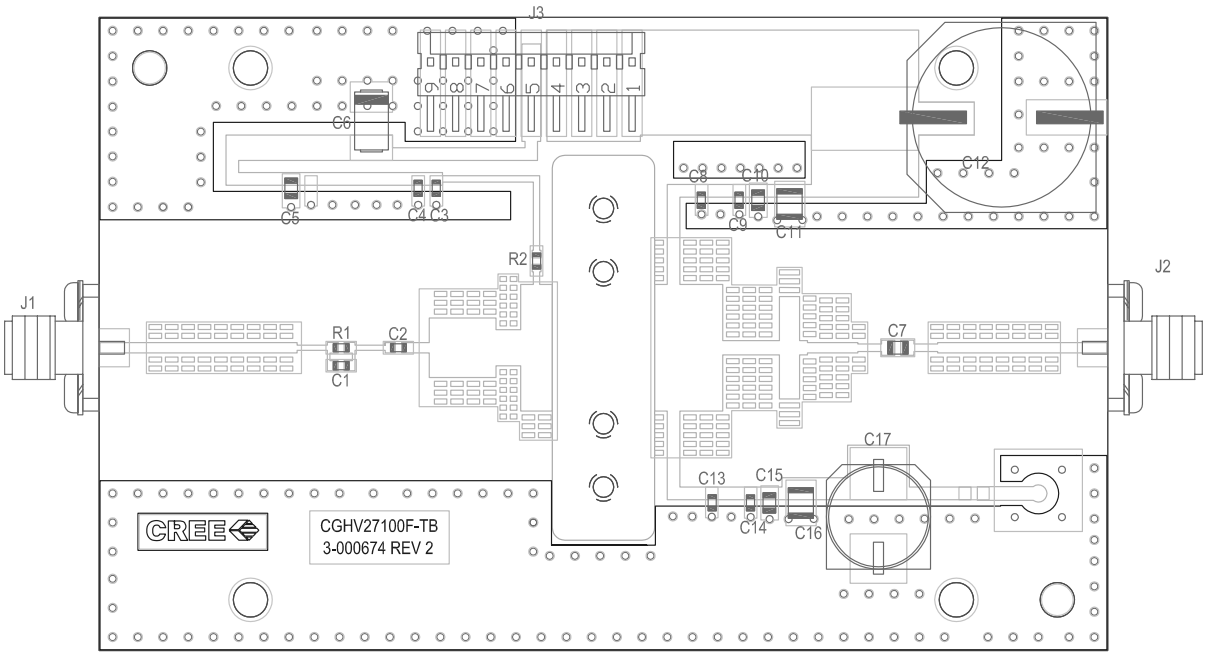
CGHV27100-AMP Demonstration Amplifier Circuit Schematic



CGHV27100-AMP Demonstration Amplifier Circuit Outline



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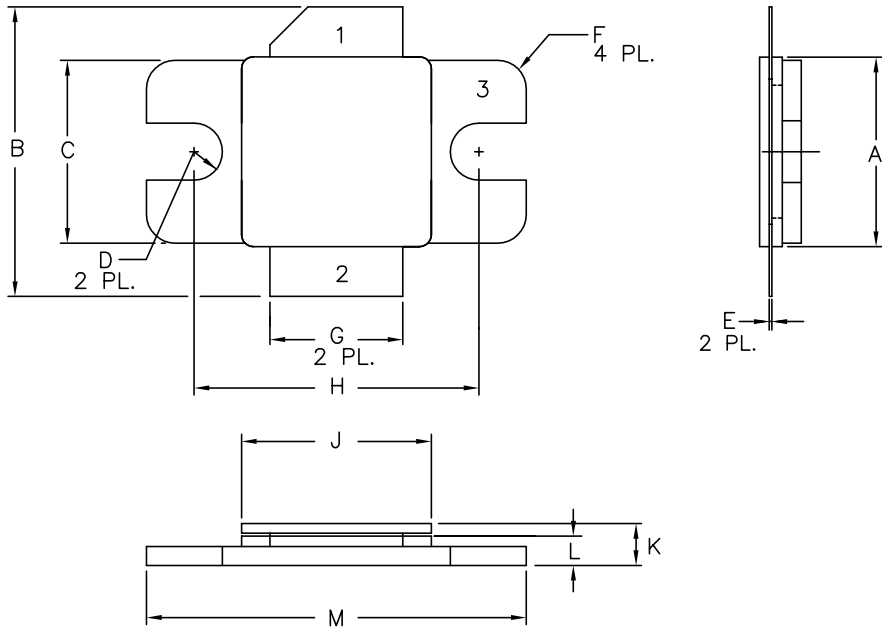
Product Dimensions CGHV27100F (Package Type — 440162)



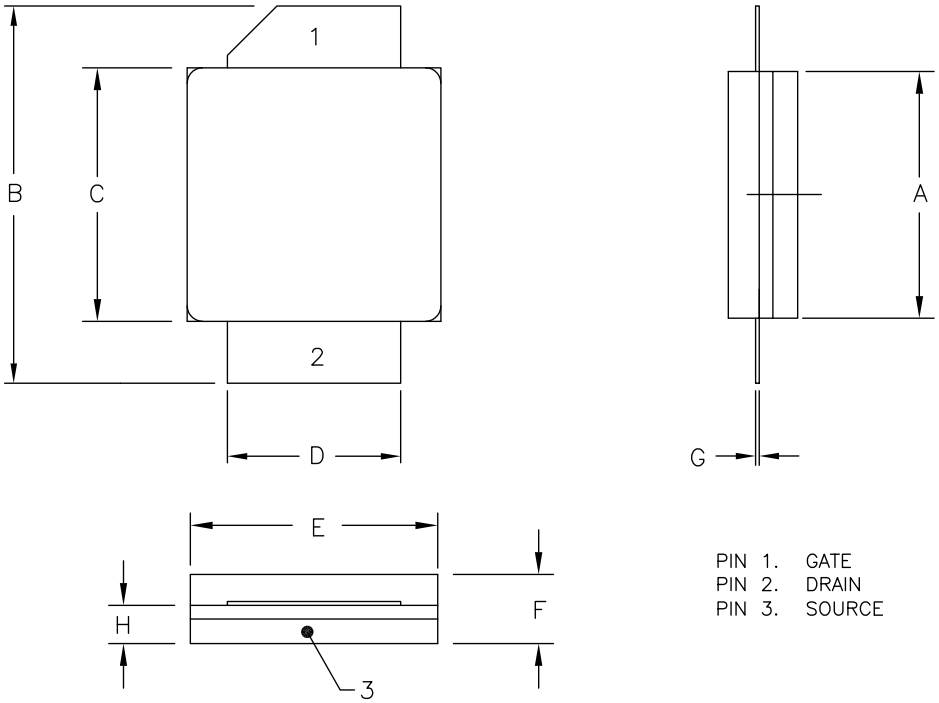
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.395	.405	10.03	10.29
B	.580	.620	14.73	15.75
C	.380	.390	9.65	9.91
D	.055	.065	1.40	1.65
E	.004	.006	0.10	0.15
F	.055	.065	1.40	1.65
G	.275	.285	6.99	7.24
H	.595	.605	15.11	15.37
J	.395	.405	10.03	10.29
K	.129	.149	3.28	3.78
L	.053	.067	1.35	1.70
M	.795	.805	20.19	20.45

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Product Dimensions CGHV27100P (Package Type — 440161)



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DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.395	.407	10.03	10.34
B	.594	.634	15.09	16.10
C	.395	.407	10.03	10.34
D	.275	.285	6.99	7.24
E	.395	.407	10.03	10.34
F	.129	.149	3.28	3.78
G	.004	.006	0.10	0.15
H	.057	.067	1.45	1.70

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

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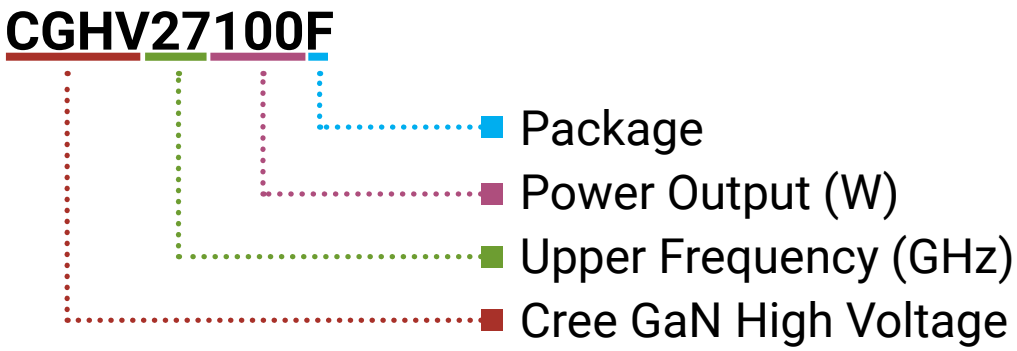
Part Number System



Parameter	Value	Units
Upper Frequency[1]	2.7	GHz
Power Output	100	W
Package	Flange	-

Table 1.

Note[1]: Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples:	1A = 10.0 GHz 2H = 27.0 GHz

Table 2.

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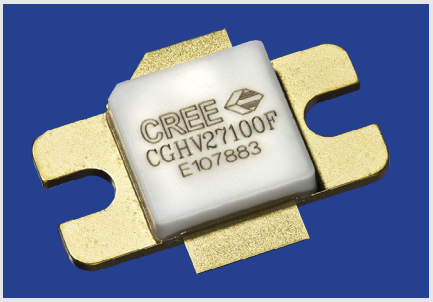
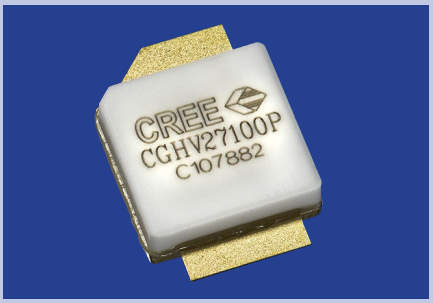
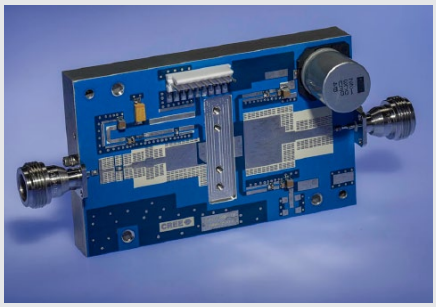
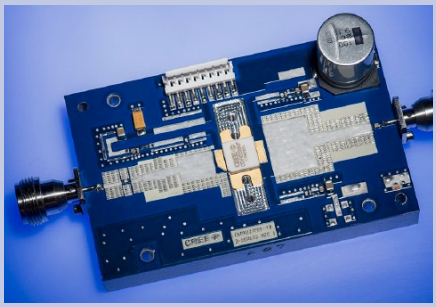
Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGHV27100F	GaN HEMT	Each	
CGHV27100P	GaN HEMT	Each	
CGHV27100-TB	Test board without GaN HEMT	Each	
CGHV27100F-AMP	Test board with GaN HEMT installed	Each	

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